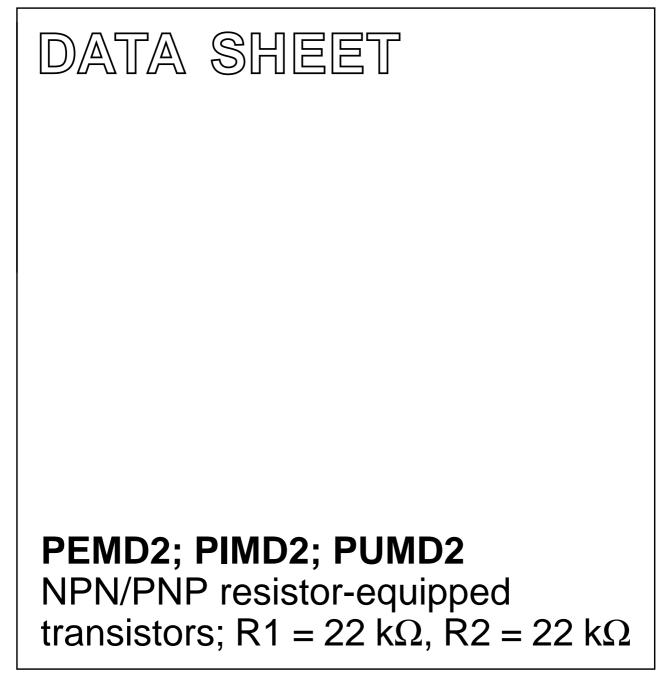
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2003 Jun 06 2004 Apr 21



PEMD2; PIMD2; PUMD2

FEATURES

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- · Reduces pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-	50	V
lo	output current (DC)	-	100	mA
TR1	NPN (PIMD2: PNP)	-	_	-
TR2	PNP (PIMD2: NPN)	-	-	-
R1	bias resistor	22	-	kΩ
R2	bias resistor	22	-	kΩ

DESCRIPTION

NPN/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

ТҮРЕ	PACKAGE			PNP/PNP	NPN/NPN
NUMBER	PHILIPS	EIAJ		COMPLEMENT	COMPLEMENT
PEMD2	SOT666	_	D4	PEMB1	PEMH1
PIMD2	SOT457	SC-74	M5	-	_
PUMD2	SOT363	SC-88	D*2 ⁽¹⁾	PUMB1	PUMH1

Note

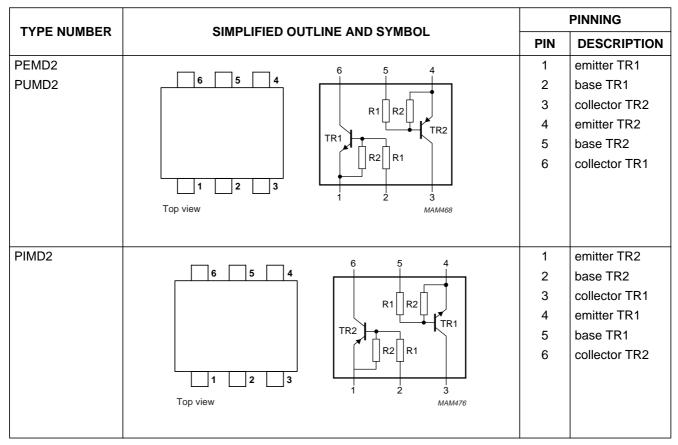
1. * = p: Made in Hong Kong.

* = t: Made in Malaysia.

* = W: Made in China.

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING



ORDERING INFORMATION

	PACKAGE				
	NAME	DESCRIPTION	VERSION		
PEMD2	 plastic surface mounted package; 6 leads SOT 		SOT666		
PIMD2	 plastic surface mounted package; 6 leads SC 		SOT457		
PUMD2	-	plastic surface mounted package; 6 leads	SOT363		

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transistor; for the PNP transistor with negative polarity						
V _{CBO}	collector-base voltage	open emitter	-	50	V	
V _{CEO}	collector-emitter voltage	open base	_	50	V	
V _{EBO}	emitter-base voltage	open collector	-	10	V	
VI	input voltage TR1					
	positive		_	+40	V	
	negative		_	-10	V	
VI	input voltage TR2					
	positive		_	+10	V	
	negative		_	-40	V	
lo	output current (DC)		-	100 mA		
I _{CM}	peak collector current		_	100 mA		
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363	note 1	_	200	mW	
	SOT457	note 1	_	300	mW	
	SOT666	notes 1 and 2	_	200	mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T _{amb}	operating ambient temperature –65 +150		+150	°C		
Per device		,				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363	note 1	_	300	mW	
	SOT457	note 1	_	600	mW	
	SOT666	notes 1 and 2	_	300	mW	

Notes

1. Refer to standard mounting conditions.

2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	tor	•		
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT363	note 1	625	K/W
	SOT457	note 1	417	K/W
	SOT666	notes 1 and 2	625	K/W
Per device		•		
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT363	note 1	416	K/W
	SOT457	note 1	208	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

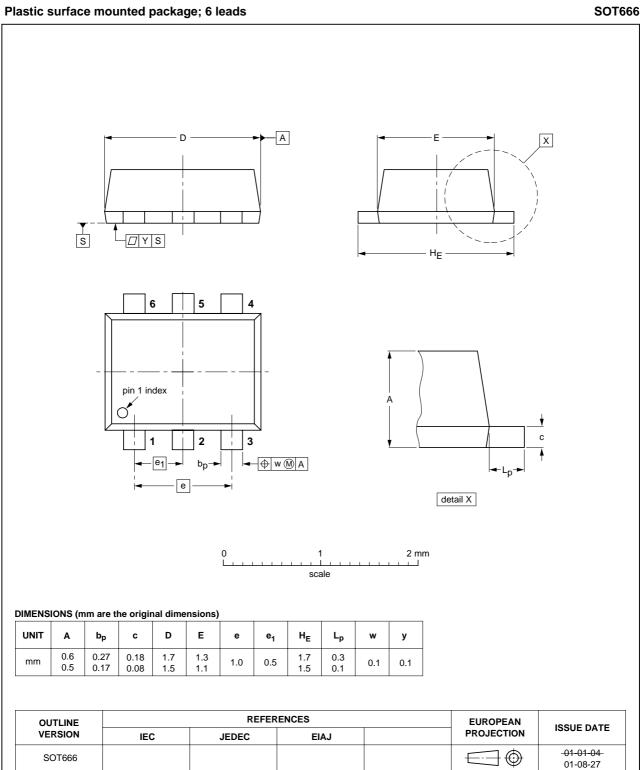
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	stor; for the PNP transistor with ne	gative polarity		•		
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	_	-	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A	-	-	1	μA
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	-	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	-	-	180	μA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 5 \text{ mA}$	60	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	-	-	150	V
V _{i(off)}	input-off voltage	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 100 \mu\text{A}$	-	1.1	0.8	V
V _{i(on)}	input-on voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	2.5	1.7	-	V
R1	input resistor		15.4	22	28.6	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

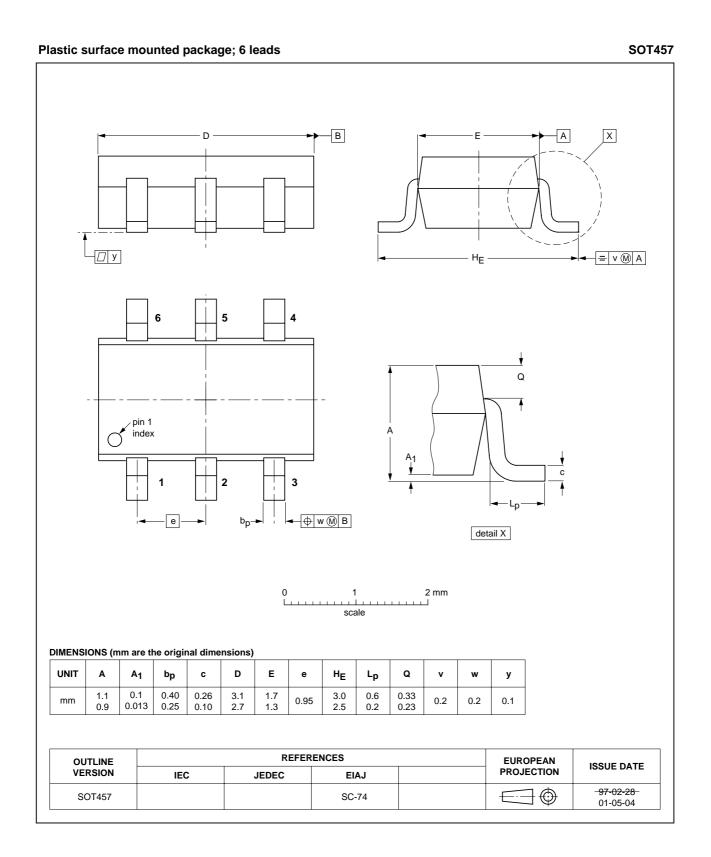
PEMD2; PIMD2; PUMD2

NPN/PNP resistor-equipped transistors; $R1 = 22 \text{ k}\Omega$, $R2 = 22 \text{ k}\Omega$

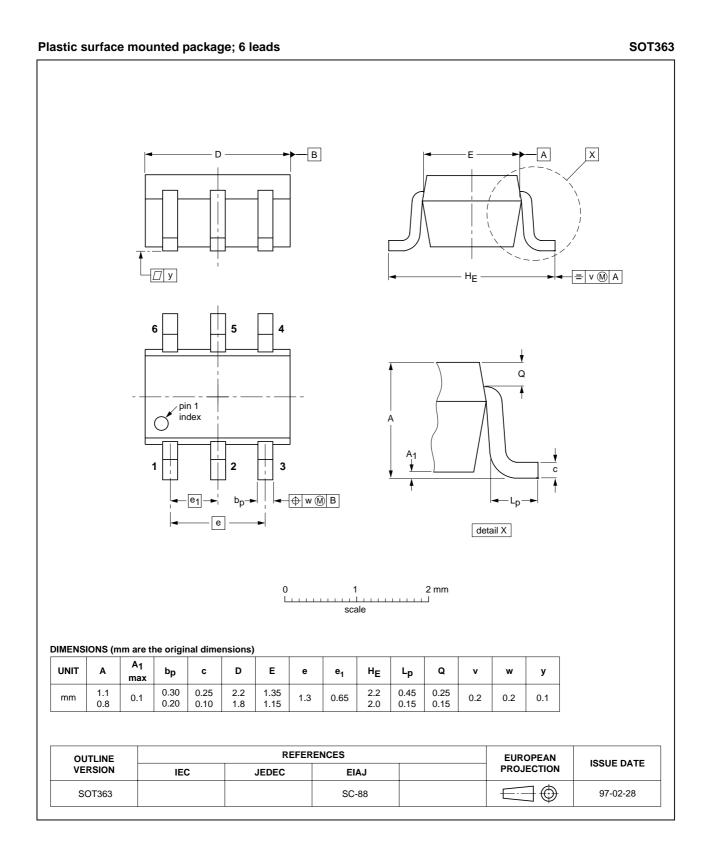
PACKAGE OUTLINES



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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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